Elektronische Bauelemente

2SB1322A

-1A , -60V

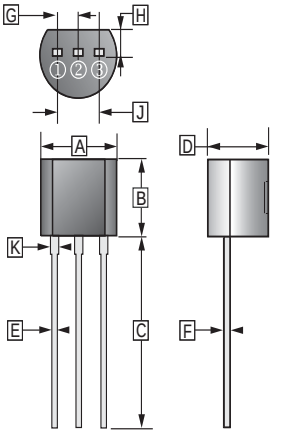
PNP Plastic Encapsulated Transistor

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

TO-92

FEATURES

- Allow Supply with The Radial Taping

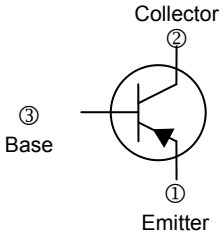


①Emitter
②Collector
③Base

REF.	Millimeter	
	Min.	Max.
A	4.40	4.70
B	4.30	4.70
C	12.70	-
D	3.30	3.81
E	0.36	0.56
F	0.36	0.51
G	1.27 TYP.	
H	1.10	-
J	2.42	2.66
K	0.36	0.76

CLASSIFICATION OF $h_{FE\ (1)}$

Product-Rank	2SB1322A-Q	2SB1322A-R	2SB1322A-S
Range	85~170	120~240	170~340



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-60	V
Collector to Emitter Voltage	V_{CEO}	-50	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-1	A
Collector Power Dissipation	P_C	0.625	W
Thermal Resistance From Junction to Ambient	$R_{\theta JA}$	200	°C / W
Junction, Storage Temperature	T_J, T_{STG}	150, -55~150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test condition
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	-60	-	-	V	I_C= -0.01mA, I_E=0
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	-50	-	-	V	I_C= -2mA, I_B=0
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	-5	-	-	V	I_E= -0.01mA, I_C=0
Collector Cut-Off Current	I_{CBO}	-	-	-0.1	μA	V_{CB}= -20V, I_E=0
Emitter Cut-Off Current	I_{EBO}	-	-	-0.1	μA	V_{EB}= -5V, I_C=0
DC Current Gain	$h_{FE\ (1)}$	85	-	340		V_{CE}= -10V, I_C= -0.5A
	$h_{FE\ (2)}$	50	-	-		V_{CE}= -5V, I_C= -1A
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	-	-	-0.4	V	I_C= -0.5A, I_B= -0.05A
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	-	-	-1.2	V	I_C= -0.5A, I_B= -0.05A
Collector-Base Capacitance	C_{cb}	-	-	30	pF	V_{CB} = -10V, I_E=0, f=1MHz
Transition Frequency	f_T	-	200	-	MHz	V_{CE} = -10V, I_C = -0.05A, f=200MHz